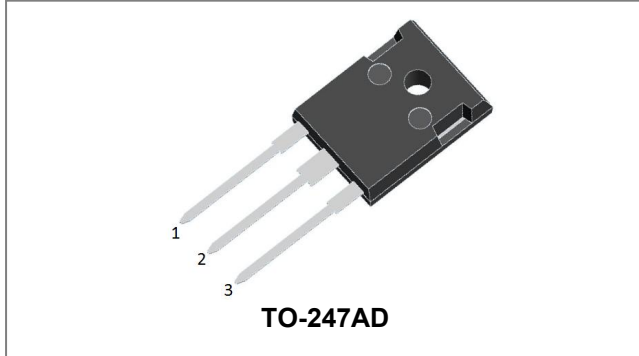


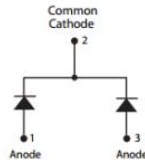
MBR3035WT/MBR3040WT/MBR3045WT **SCHOTTKY RECTIFIER**



Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings@T_c=25°C unless otherwise specified

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	35	V
Working Peak Reverse Voltage	V _{RWM}		40	
DC Blocking Voltage	V _R		45	
Average Rectified Forward Current	I _{F(AV)}	T _c =145°C, In DC	15(Per Leg) 30(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	240	A
Peak Repetitive Forward Current (per leg)	I _{FRM}	Rated V _R ,square wave, 20KHz T _c =123 °C	30	A
Peak Repetitive Reverse Current	I _{RRM}	2.0µsec 1.0KHz	2.0	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (Per Leg)*	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.59	0.70	V
		@ 30A, Pulse, T _J = 25 °C	0.76	0.84	
Reverse Current (Per Leg)*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.04	1.0	mA
		@V _R = rated V _R , T _J = 125 °C	19	100	
Junction Capacitance(Per Leg)	C _T	@V _R = 5V, T _C = 25 °C, f _{sig} = 1MHz	541	800	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/µs

* Pulse width < 300 µs, duty cycle < 2%

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case(Per Leg)	$R_{\theta\text{JC}}$	DC operation	0.5	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

Ratings and Characteristics Curves

Figure 1 Typical Forward Characteristics

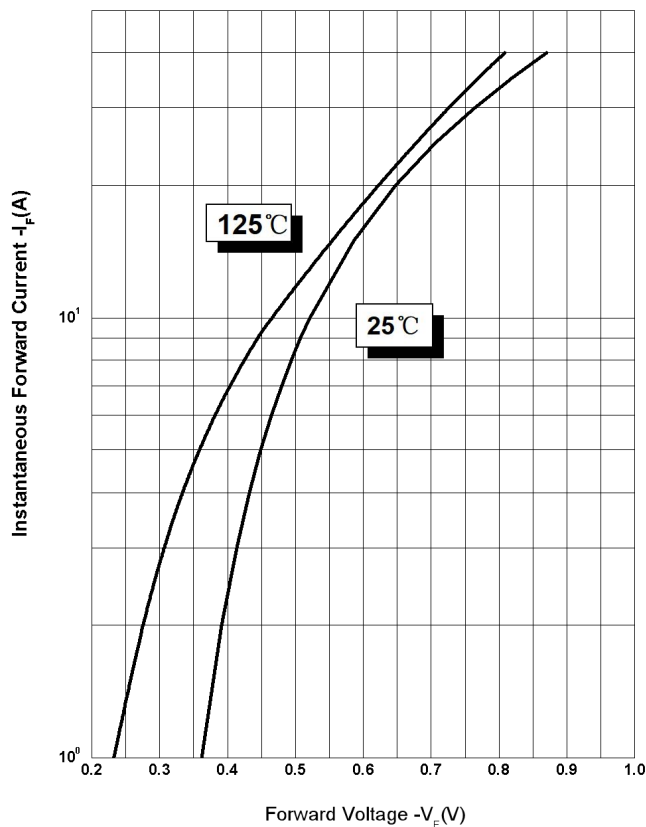


Figure 2 Typical Reverse Characteristics

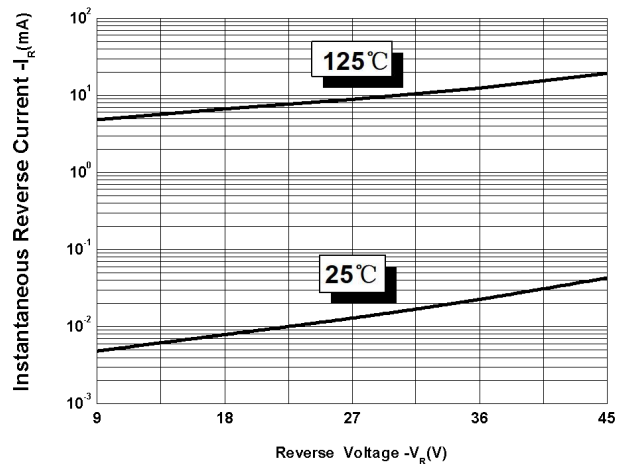
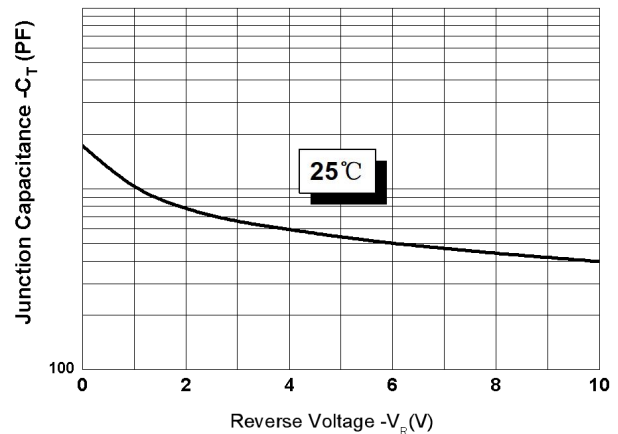
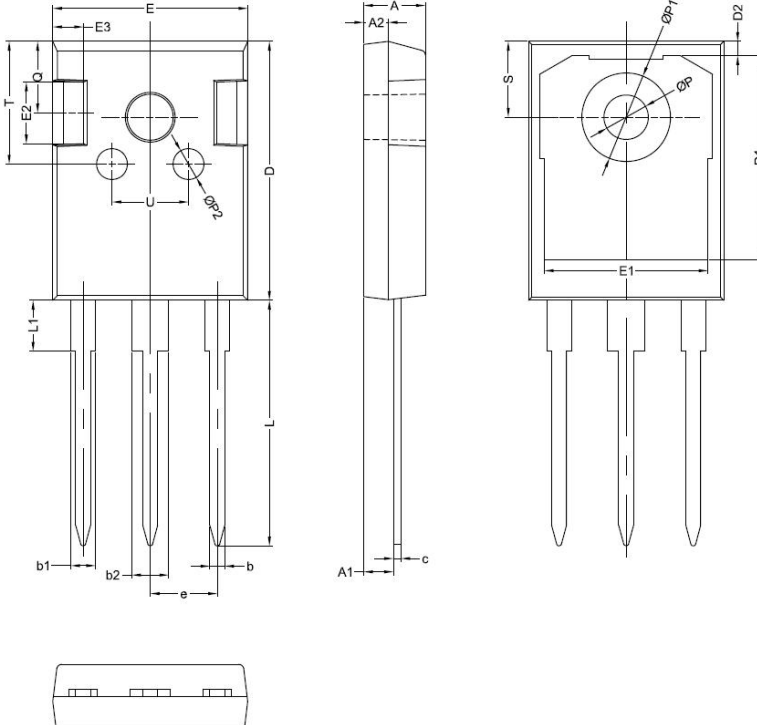


Figure 3 Typical Junction Capacitance



Mechanical Dimensions TO-247AD

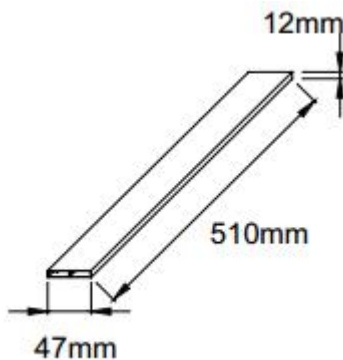


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.40
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.55	
D2		1.20	
E	15.45	15.80	16.00
E1		13.30	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.70
L1		4.13	
P	3.50	3.60	3.70
P1	7.1		7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

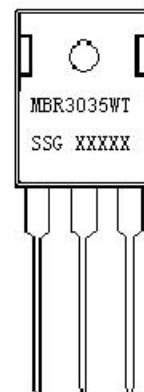
Ordering Information:

Device	Package	Shipping
MBR3035WT-MBR3045WT	TO-247AD(Pb-Free)	25pcs / tube

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

- MBR = Device Type
- 30 = Forward Current (30A)
- 35 = Reverse Voltage (35V)
- WT = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0



MBR3035WT
MBR3040WT
MBR3045WT

Technical Data
Data Sheet N0015, Rev. A



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